# NCE40H20AD

# NCE N-Channel Enhancement Mode Power MOSFET

#### **Description**

The NCE40H20AD uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

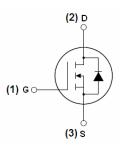
- $V_{DS} = 40V, I_D = 200A$  $R_{DS(ON)} < 2.6mΩ @ V_{GS} = 10V$  (Typ:2.0mΩ)
- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation

#### **Application**

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



#### Schematic diagram



Marking and pin assignment



TO-263-2L top view

#### **Package Marking and Ordering Information**

	,	9			
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE40H20AD	NCE40H20AD	TO-263-2L	-	_	-

## Absolute Maximum Ratings (T<sub>C</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	40	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	200	Α
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	140	Α
Pulsed Drain Current	I <sub>DM</sub>	790	А
Maximum Power Dissipation	P <sub>D</sub>	285	W
Derating factor		1.9	W/°C
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	2500	mJ
Operating Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 To 175	$^{\circ}$ C



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# NCE40H20AD

# **Thermal Characteristic**

Thermal Resistance, Junction-to-Case (Note 2)	R <sub>θJc</sub>	0.53	°C/W	
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## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)	<u>.</u>					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =40A	-	2.0	2.6	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =40A	60	-	-	S
Dynamic Characteristics (Note4)			•			•
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V,	-	7182	-	PF
Output Capacitance	Coss		-	1355	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UIVIHZ	-	1244	-	PF
Switching Characteristics (Note 4)	<u>.</u>					
Turn-on Delay Time	t <sub>d(on)</sub>		-	21	-	nS
Turn-on Rise Time	t <sub>r</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =40A V <sub>DS</sub> =5V,I <sub>D</sub> =40A V <sub>DS</sub> =5V,V <sub>GS</sub> =0V, F=1.0MHz  V <sub>DD</sub> =20V,V <sub>GS</sub> =10V, R <sub>GEN</sub> =2.5Ω V <sub>DS</sub> =20V,I <sub>D</sub> =20A, V <sub>GS</sub> =10V	-	37	-	nS
Turn-Off Delay Time	$t_{\sf d(off)}$	$R_{GEN}$ =2.5 $\Omega$	-	75	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	40	-	nS
Total Gate Charge	Qg	)/ 00\/ L 00A	-	130	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =20V,I <sub>D</sub> =20A,	-	36	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	56	-	nC
Drain-Source Diode Characteristics	<u>.</u>					
Diode Forward Voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V,I <sub>S</sub> =20A	-	-	1.2	V
Diode Forward Current (Note 2)	Is	-	-	-	200	Α
Reverse Recovery Time	t <sub>rr</sub>	t <sub>rr</sub> TJ = 25°C, IF = 20A - 50		-	nS	
Reverse Recovery Charge	Qrr	t <sub>rr</sub> TJ = 25°C, IF = 20A - 50		61	-	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negl	igible (turi	n-on is do	minated b	y LS+LD)

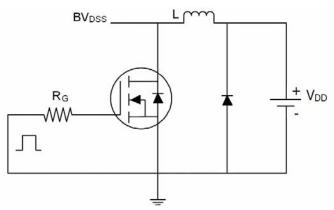
# Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}$ C,V<sub>DD</sub>=20V,V<sub>G</sub>=10V,L=0.5mH,Rg=25 $\Omega$

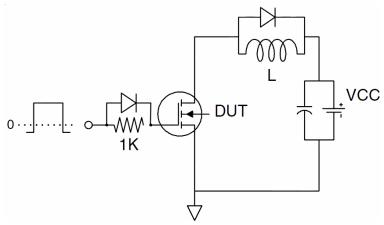


# **Test circuit**

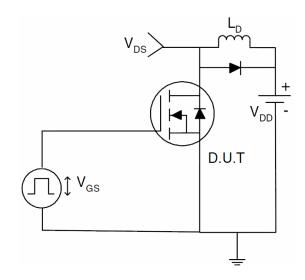
# 1) E<sub>AS</sub> test Circuits



# 2) Gate charge test Circuit:



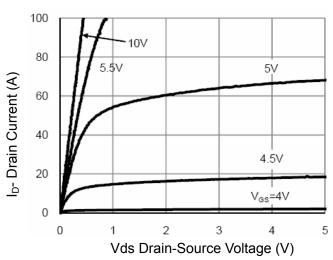
## 3) Switch Time Test Circuit:



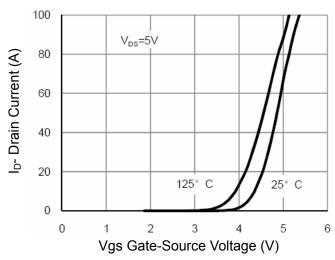
**Pb Free Product** 



# **Typical Electrical and Thermal Characteristics (Curves)**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

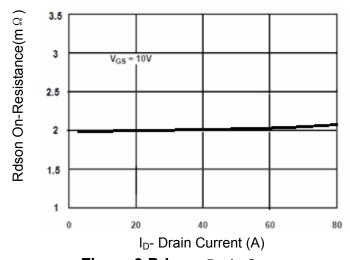


Figure 3 Rdson- Drain Current

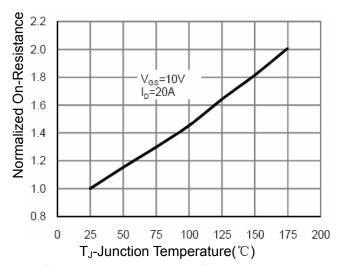


Figure 4 Rdson-JunctionTemperature

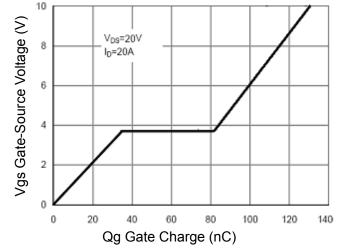


Figure 5 Gate Charge

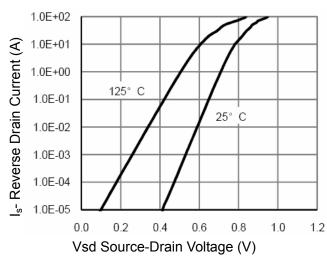


Figure 6 Source- Drain Diode Forward



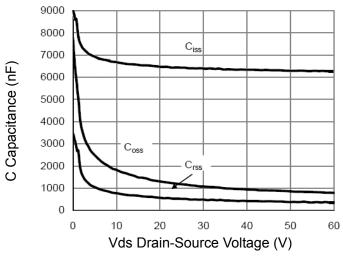


Figure 7 Capacitance vs Vds

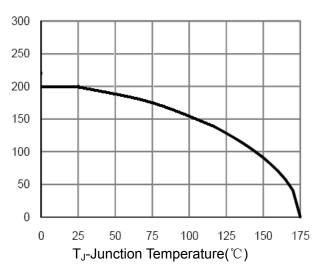


Figure 9 Current De-rating

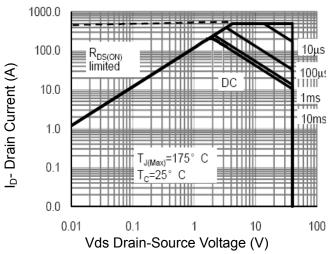


Figure 8 Safe Operation Area

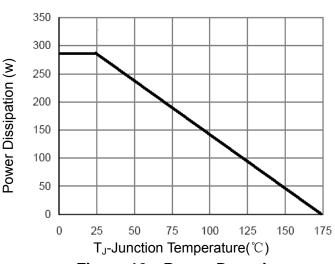
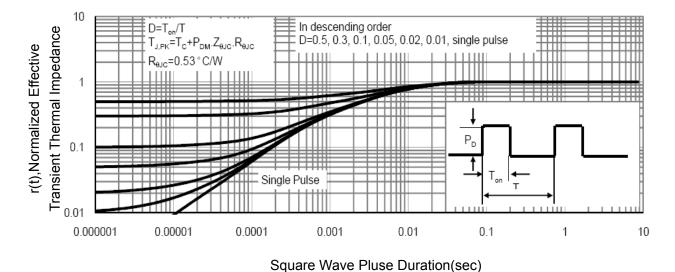


Figure 10 Power De-rating



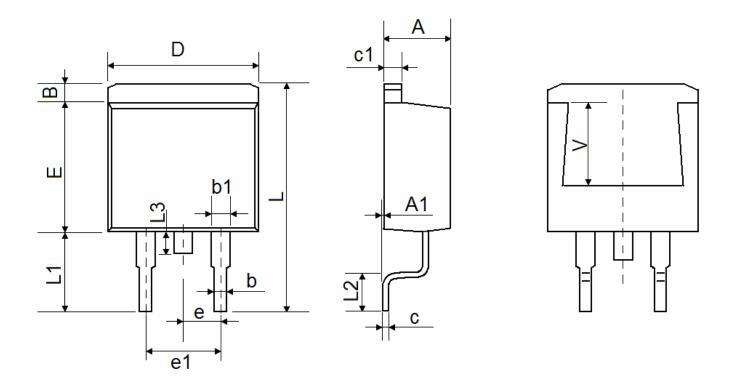
**Figure 11 Normalized Maximum Transient Thermal Impedance** 

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# **TO-263-2L Package Information**



Dimensions	In Millimeters	Dimensions In Inches		
Min.	Max.	Min.	Max.	
4.470	4.670	0.176	0.184	
0.000	0.150	0.000	0.006	
1.170	1.370	0.046	0.054	
0.710	0.910	0.028	0.036	
1.170	1.370	0.046	0.054	
0.310	0.530	0.012	0.021	
1.170	1.370	0.046	0.054	
10.010	10.310	0.394	0.406	
8.500	8.900	0.335	0.350	
2.540	TYP.	0.100 TYP.		
4.980	5.180	0.196	0.204	
15.050	15.450	0.593	0.608	
5.080	5.480	0.200	0.216	
2.340	2.740	0.092	0.108	
1.300	1.700	0.051	0.067	
	Min. 4.470 0.000 1.170 0.710 1.170 0.310 1.170 10.010 8.500 2.540 4.980 15.050 5.080 2.340	4.470       4.670         0.000       0.150         1.170       1.370         0.710       0.910         1.170       1.370         0.310       0.530         1.170       1.370         10.010       10.310         8.500       8.900         2.540 TYP.         4.980       5.180         15.050       15.450         5.080       5.480         2.340       2.740	Min.         Max.         Min.           4.470         4.670         0.176           0.000         0.150         0.000           1.170         1.370         0.046           0.710         0.910         0.028           1.170         1.370         0.046           0.310         0.530         0.012           1.170         1.370         0.046           10.010         10.310         0.394           8.500         8.900         0.335           2.540 TYP.         0.100           4.980         5.180         0.196           15.050         15.450         0.593           5.080         5.480         0.200           2.340         2.740         0.092	



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